

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New Patent Application of)
Taketomi ASAMI et al.)
Japanese Priority Application No. 2000-131353) Attn: Applications
Japanese Priority Date: April 28, 2000) Branch
For: MANUFACTURING METHOD FOR)
SEMICONDUCTOR DEVICE) Date: April 26, 2001

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE SPECIFICATION:

Please amend specification as follows: Please note that the specification is presented below in its amended form. It is further presented as an Attachment to the Amendment whereby the amendments to the specification are outlined using the conventional method of bracketing and underlining.

Please amend the BRIEF DESCRIPTION OF THE DRAWINGS on pages 4 and 5 as follows:

Figs. 2A, 2B, and 2C are cross sectional views of a TFT according to the example 1;

Figs. 3A, 3B, and 3C are cross sectional views of a TFT according to the example 1;

Figs. 4A and 4B are cross sectional views of a TFT according to the example 1;

Figs. 7A, and 7B are top views and a cross section view of an EL display panel according to the example 3;

Figs. 8A and 8B are cross sectional views of an EL display panel according to the example 3;

Figs. 10A, 10B, 10C, 10D, 10E and 10F are views showing a variety of semiconductor devices according to the example 4;

Figs. 11A, 11B, 11C and 11D are views showing a variety of semiconductor devices according to the example 4; and


Figs. 12A, 12B and 12C are views showing a variety of semiconductor devices according to the example 4.

REMARKS

The specification has been amended to correct the descriptions of Figures 2-4, 7, 8, and 10-12 in the Brief Descriptions of the Drawings.

Examination on the merits is requested.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

[Fig. 2 is a cross section view] Figs. 2A, 2B, and 2C are cross sectional views of a TFT according to the example 1;

[Fig. 3 is a cross section view] Figs. 3A, 3B, and 3C are cross sectional views of a TFT according to the example 1;

[Fig. 4 is a cross section view] Figs. 4A and 4B are cross sectional views of a TFT according to the example 1;

[Fig. 7 is a top view] Figs. 7A, and 7B are top views and a cross section view of an EL display panel according to the example 3;

[Fig. 8 is a cross section view] Figs. 8A and 8B are cross sectional views of an EL display panel according to the example 3;

[Fig. 10 is a view] Figs. 10A, 10B, 10C, 10D, 10E and 10F are views showing a variety of semiconductor devices according to the example 4;

[Fig. 11 is a view] Figs. 11A, 11B, 11C and 11D are views showing a variety of semiconductor devices according to the example 4; and

[Fig. 12 is a view] Figs. 12A, 12B and 12C are views showing a variety of semiconductor devices according to the example 4.